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2:1 MIPI D-PHY (1.5 Gbps) 4 Data Lane Switch

FSA634

Description

The FSA634 is configured as a 4 data lane, MIPI D–PHY switch. This single pole double throw (SPDT) switch is optimized for switching between two high speed or low power MIPI sources. The FSA634 is designed for the MIPI specification and allows connection to a CSI or DSI module.

Features

- Switch Type: SPDT (10x)
- Signal Type: MIPI, D-PHY
- V_{CC}: 1.65 to 4.5 V
- Input Signal: 0 V to V_{CC}
- R_{ON}:
 - 5 Ω Typical HS MIPI
 - 5 Ω Typical LP MIPI
- ΔR_{ON} : 0.1 Ω Typical
- R_{ON_FLAT} : 0.06 Ω Typical
- I_{CCZ}: 0.5 µA Maximum
- I_{CC}: 32 μA Maximum
- O_{IRR}: -30 dB Typical
- Bandwidth: 1.9 GHz Typical
- Xtalk: -38 dB Typical
- C_{ON}: 4.3 pF Typical
- Skew: 3 ps Typical

Applications

- Cellular Phones, Smart Phones
- Tablets
- Laptops
- Displays



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(Bottom View)

WLCSP36, 2.06x2.06x0.432 CASE 567XU

MARKING DIAGRAM



- = Specific Device Code
- KK = Assembly Lot
 - = Year

VJ

Х

Υ

Ζ

- = Work Week
- = Assembly Location

ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet.

1

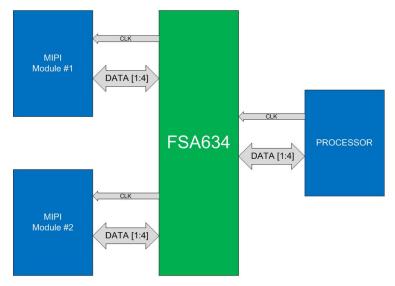
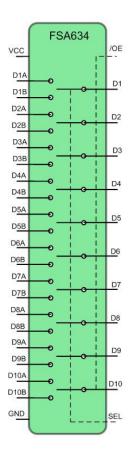
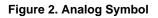


Figure 1. Typical Application

PIN DESCRIPTIONS



PIN NAME	DESCRIPTION				
Dn	Common Data Path				
DnA	Data Path	Data Path A			
DnB	Data Path B				
/OE	Output Enable				
051	Control	SEL=0	Dn = DnA		
SEL	Pin	SEL=1	Dn = DnB		
VCC	Power				
GND	Ground				
NC	No Conne	ect			



PIN DEFINITIONS

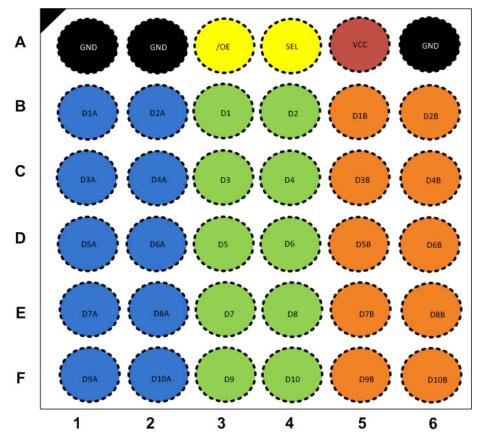


Figure 3. Top Through View

Ball	Pin Name	Ball	Pin Name	Ball	Pin Name
A1	GND	C1	D3A	E1	D7A
A2	GND	C2	D4A	E2	D8A
A3	/OE	C3	D3	E3	D7
A4	SEL	C4	D4	E4	D8
A5	V _{CC}	C5	D3B	E5	D7B
A6	GND	C6	D4B	E6	D8B
B1	D1A	D1	D5A	F1	D9A
B2	D2A	D2	D6A	F2	D10A
B3	D1	D3	D5	F3	D9
B4	D2	D4	D6	F4	D10
B5	D1B	D5	D5B	F5	D9B
B6	D2B	D6	D6B	F6	D10B

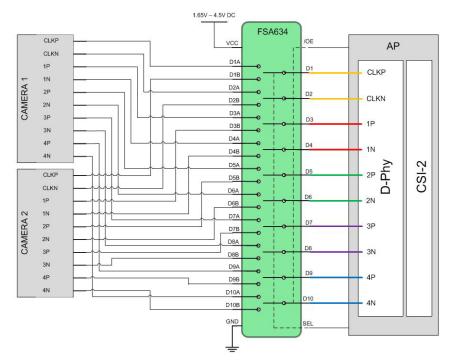


Figure 4. Suggested Configuration for 4 Lane D-PHY

TRUTH TABLE

SEL	/OE	Function
LOW	LOW	Dn = DnA
HIGH	LOW	Dn = DnB
X	HIGH	All Ports High Impedance

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Min	Max	Unit
V _{CC}	Supply Voltage			5.25	V
V _{CNTRL}	DC Input Voltage (/OE, SEL)	-0.5	V _{CC}	V	
V _{SW}	DC Switch I/O Voltage	-0.3	V _{CC}	V	
I _{IK}	DC Input Diode Current	-50		mA	
I _{OUT}	DC Output Current			50	mA
T _{STG}	Storage Temperature	-65	+150	°C	
ESD	Human Body Model, JEDEC: JESD22-A114	All Pins	3.5		kV
	Charged Device Model, JEDEC: JESD22-C101		1.5		

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

The input and output negative ratings may be exceeded if the input and output diode current ratings are observed.
V_{SW} refers to analog data switch paths.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{CC}	Supply Voltage		1.65	4.50	V
V _{CNTRL}	Control Input Voltage (SEL, /OE) (Note 3)		0	V _{CC}	V
V _{SW}		S Mode	0	0.425	V
	(Dn, DAn, DBn)	P Mode	0	1.3	V
T _A	Operating Temperature		-40	+85	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.The control inputs must be held HIGH or LOW; they must not float.

ELECTRICAL SPECIFICATION TABLE Typical values are at $T_A = 25^{\circ}C$, $V_{CC} = 3.3$ V unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
C ELECTRICAL PARA	METERS					
V _{IK}	Clamp Diode Voltage	$I_{IN} = -18 \text{ mA}, V_{CC} = 1.8 \text{ V}$			-1.2	V
V _{IH}	Input Voltage High	$V_{CC} = 1.65 \text{ V to } 4.50 \text{ V}$	1.0			V
V _{IL}	Input Voltage Low	$V_{CC} = 1.65 \text{ V to } 4.50 \text{ V}$			0.4	V
I _{IN}	Control Input Leakage (SEL,/OE)	$V_{SW} = 0$ V to V_{CC} , $V_{CC} = 1.65$ V to 4.50 V	-500		500	nA
$IN_{O(OFF)},IN_{C(OFF)}$	Off Leakage Current of Port Dn, DnA, DnB	$ \begin{array}{l} {\sf Dn} = 0.3 \; {\sf V} \; {\rm to} \; {\sf V}_{\rm CC} - 0.3 \; {\sf V}; \; {\sf DnA} \; {\rm or} \; {\sf DnB} = \\ {\sf Floating}, \; 0.3 \; {\sf V}, \; {\rm or} \; {\sf V}_{\rm CC} - 0.3 \; {\sf V}; \; / {\sf OE} = 0 \; {\sf V}; \\ {\sf V}_{\rm CC} = 1.65 \; {\sf V} \; {\rm to} \; 4.5 \; {\sf V} \end{array} $	-500		500	nA
I _{A(ON)}	On Leakage Current of Common Ports (Dn)		-500		500	nA
I _{OFF}	Power–Off Leakage Current	Dn, DnA or DnB; $V_{IN} = 0 V$ to 4.5 V; $V_{CC} = 0 V$	-500		500	nA
IOZ	Off-State Leakage	0 \leq Dn, DnA, DnB \leq 3.6 V, /OE = High, V_{CC} = 4.5 V	-500		500	nA
R _{ON_MIPI_HS_1p8}	Switch On Resistance for HS MIPI Applications	$I_{ON} = -10 \text{ mA}$, /OE = 0 V, SEL = V _{CC} or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, V _{CC} = 1.8 V		5	12	Ω
R _{ON_MIPI_HS_2p5}	— (Note 5)	$I_{ON} = -10 \text{ mA}$, /OE = 0 V, SEL = V _{CC} or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, V _{CC} = 2.5 V		5	9	Ω
R _{ON_MIPI_HS_3p6}		$I_{ON} = -10 \text{ mA}$, /OE = 0 V, SEL = V _{CC} or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, V _{CC} = 3.6 V		5	9	Ω
R _{ON_MIPI_HS_4p5}		$I_{ON} = -10 \text{ mA}$, /OE = 0 V, SEL = V _{CC} or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, V _{CC} = 4.5 V		5	9	Ω
R _{ON_MIPI_LP_1p8}	Switch On Resistance for LP MIPI Applications	$I_{ON} = -10 \text{ mA}$, /OE = 0 V, SEL = V _{CC} or 0 V, DnA or DnB = 0 V, 0.6 V, 1.2 V, V _{CC} = 1.8 V		5	12	Ω
R _{ON_MIPI_LP_2p5}	(Note 5)	$I_{ON} = -10 \text{ mA}$, /OE = 0 V, SEL = V _{CC} or 0 V, DnA or DnB = 0 V, 0.6 V, 1.2 V, V _{CC} = 2.5 V		5	9	Ω
R _{ON_MIPI_LP_3p6}		$I_{ON} = -10 \text{ mA}$, /OE = 0 V, SEL = V _{CC} or 0 V, DnA or DnB = 0 V, 0.6 V, 1.2 V, V _{CC} = 3.6 V		5	9	Ω
R _{ON_MIPI_LP_4p5}		I _{ON} = -10 mA, /OE = 0 V, SEL = V _{CC} or 0 V, DnA or DnB = 0 V, 0.6 V, 1.2 V V _{CC} = 4.5 V		5	9	Ω

Symbol	Parameter	Conditions	Min	Тур	Max	Units
C ELECTRICAL PARAN	IETERS					
$\Delta R_{ON_MIPI_HS_1p8}$	Between HS MIPI Chan-	$I_{ON} = -10 \text{ mA}$, /OE = 0 V, SEL = V _{CC} or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, V _{CC} = 1.8 V		0.10		Ω
$\Delta R_{ON_MIPI_HS_{2p5}}$	-nels	$ I_{ON} = -10 \text{ mA}, /OE = 0 \text{ V}, \text{ SEL} = \text{V}_{CC} \text{ or } 0 \text{ V}, \\ \text{DnA or DnB} = 0.1 \text{ V}, 0.2 \text{ V}, 0.3 \text{ V}, \text{V}_{CC} = 2.5 \text{ V} $		0.10		Ω
$\Delta R_{ON_MIPI_HS_3p6}$		$ I_{ON} = -10 \text{ mA}, /OE = 0 \text{ V}, \text{ SEL} = \text{V}_{CC} \text{ or } 0 \text{ V}, \\ \text{DnA or DnB} = 0.1 \text{ V}, 0.2 \text{ V}, 0.3 \text{ V}, \text{V}_{CC} = 3.6 \text{ V} $		0.10		Ω
$\Delta R_{ON_MIPI_HS_4p5}$		$I_{ON} = -10 \text{ mA}$, /OE = 0 V, SEL = V _{CC} or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, V _{CC} = 4.5 V		0.10		Ω
$\Delta R_{ON_MIPI_LP_1p8}$	On Resistance Matching Between LP MIPI Chan-	$I_{ON} = -10 \text{ mA}$, /OE = 0 V, SEL = V _{CC} or 0 V, DnA or DnB = 0.0 V, 0.6 V, 1.2 V, V _{CC} = 1.8 V		0.12		Ω
$\Delta R_{ON_MIPI_LP_2p5}$	-nels	$I_{ON} = -10 \text{ mA}$, /OE = 0 V, SEL = V _{CC} or 0 V, DnA or DnB = 0.0 V, 0.6 V, 1.2 V, V _{CC} = 2.5 V		0.12		Ω
$\Delta R_{ON_MIPI_LP_3p6}$		$I_{ON} = -10 \text{ mA}, /OE = 0 \text{ V}, \text{ SEL} = V_{CC} \text{ or } 0 \text{ V}, \text{ DnA or DnB} = 0.0 \text{ V}, 0.6 \text{ V}, 1.2 \text{ V}, V_{CC} = 3.6 \text{ V}$		0.12		Ω
$\Delta R_{ON_MIPI_LP_4p5}$		$I_{ON} = -10 \text{ mA}$, /OE = 0 V, SEL = V _{CC} or 0 V, DnA or DnB = 0.0 V, 0.6 V, 1.2 V, V _{CC} = 4.5 V		0.12		Ω
R _{ON_FLAT_MIPI_HS_1p8}	On Resistance Flatness for HS MIPI Signals	$I_{ON} = -10 \text{ mA}, /OE = 0 \text{ V}, \text{ SEL} = V_{CC} \text{ or } 0 \text{ V},$ DnA or DnB = 0.1 V, 0.2 V, 0.3 V, V _{CC} = 1.8 V		0.04		Ω
R _{ON_FLAT_MIPI_HS_2p5}		$I_{ON} = -10 \text{ mA}$, /OE = 0 V, SEL = V _{CC} or 0 V, DnA or DnB = 0.1 V, 0.2 V, 0.3 V, V _{CC} = 2.5 V		0.06		Ω
R _{ON_FLAT_MIPI_HS_3p6}		$I_{ON} = -10 \text{ mA}, /OE = 0 \text{ V}, \text{ SEL} = V_{CC} \text{ or } 0 \text{ V}, \text{DnA or DnB} = 0.1 \text{ V}, 0.2 \text{ V}, 0.3 \text{ V}, V_{CC} = 3.6 \text{ V}$		0.06		Ω
R _{ON_FLAT_MIPI_HS_4p5}		$ I_{ON} = -10 \text{ mA}, /OE = 0 \text{ V}, \text{ SEL} = \text{V}_{CC} \text{ or } 0 \text{ V}, \\ \text{DnA or DnB} = 0.1 \text{ V}, 0.2 \text{ V}, 0.3 \text{ V}, \text{V}_{CC} = 4.5 \text{ V} $		0.06		Ω
R _{ON_FLAT_MIPI_LP_1p8}	On Resistance Flatness for LP MIPI Signals	$I_{ON} = -10 \text{ mA}$, /OE = 0 V, SEL = V _{CC} or 0 V, DnA or DnB = 0.0 V, 0.6 V, 1.2 V, V _{CC} = 1.8 V		0.18		Ω
R _{ON_FLAT_MIPI_LP_2p5}		$I_{ON} = -10 \text{ mA}$, /OE = 0 V, SEL = V _{CC} or 0 V, DnA or DnB = 0.0 V, 0.6 V, 1.2 V, V _{CC} = 2.5 V		0.28		Ω
R _{ON_FLAT_MIPI_LP_3p6}		$I_{ON} = -10 \text{ mA}$, /OE = 0 V, SEL = V _{CC} or 0 V, DnA or DnB = 0.0 V, 0.6 V, 1.2 V, V _{CC} = 3.6 V		0.28		Ω
R _{ON_FLAT_MIPI_LP_4p5}		$I_{ON} = -10 \text{ mA}$, /OE = 0 V, SEL = V _{CC} or 0 V, DnA or DnB = 0.0 V, 0.6 V, 1.2 V, V _{CC} = 4.5 V		0.28		Ω
I _{CCZ}	Quiescent Hi–Z Supply Current	V_{IN} = 0 V or V_{CC} , I_{OUT} = 0 A, V_{CC} = 4.5 V			0.5	μΑ
I _{CC}	Quiescent Supply Current	V_{IN} = 0 or $V_{\text{CC}},I_{\text{OUT}}$ = 0 A, V_{CC} = 2.5 V to 4.5 V		16	32	μΑ
I _{CC_1p8}	1	$V_{IN} = 0$ or V_{CC} , $I_{OUT} = 0$ A, $V_{CC} = 1.8$ V		15	25	μA
I _{CCT_4p5}	Increase in I _{CC} Current Per Control Voltage and	V_{SEL} = 1.65 V, /OE = 1.65 V, V_{CC} = 4.5 V			4	μΑ
I _{CCT_2p5}	V _{CC}	V _{SEL} = 1.65 V, /OE = 1.65 V, V _{CC} = 2.5 V			0.1	μΑ

AC ELECTRICAL PARAMETERS

t _{init}	Initalization Time V_{CC} to Output	$\rm R_L$ = 50 $\Omega, \rm C_L$ = 5 pF, $\rm V_{SW}$ = 1.2 V, $\rm V_{CC}$ = 2.5 V to 4.5 V		100	μs
t _{INIT_1p8}		R_L = 50 Ω, C_L = 5 pF, V_{SW} = 1.2 V, V_{CC} = 1.8 V		150	μs
t _{EN}	Enable Turn–On Time, /OE to Output	$\rm R_L$ = 50 $\Omega, \rm C_L$ = 5 pF, $\rm V_{SW}$ = 1.2 V, $\rm V_{CC}$ = 2.5 V to 4.5 V	120	200	ns
t _{EN_1p8}		R_{L} = 50 Ω,C_{L} = 5 pF, V_{SW} = 1.2 V, V_{CC} = 1.8 V	250	500	ns
t _{DIS}	Disable Turn-Off Time, /OE to Output	$\rm R_L$ = 50 $\Omega, \rm C_L$ = 5 pF, $\rm V_{SW}$ = 1.2 V, $\rm V_{CC}$ = 2.5 V to 4.5 V	25	50	ns
t _{DIS_1p8}		R _L = 50 Ω, C _L = 5 pF, V _{SW} = 1.2 V, V _{CC} = 1.8 V	50	90	ns

Symbol	Parameter	Conditions	Min	Тур	Max	Units
AC ELECTRICAL PAR	AMETERS			-		
t _{ON}	Turn–On Time, SEL to Output	R _L = 50 Ω, C _L = 5 pF, V _{SW} = 1.2 V, V _{CC} = 2.5 V to 4.5 V, SEL = H to L, SEL = L to H			200	ns
t _{ON_1p8}		R _L = 50 Ω, C _L = 5 pF, V _{SW} = 1.2 V, V _{CC} = 1.8 V, SEL = H to L, SEL = L to H			300	ns
t _{OFF}	Turn–Off Time SEL to Output	R _L = 50 Ω, C _L = 5 pF, V _{SW} = 1.2 V, V _{CC} = 2.5 V to 4.5 V, SEL = H to L, SEL = L to H			200	ns
t _{OFF_1p8}		$R_L = 50 \Omega$, $C_L = 5 pF$, $V_{SW} = 1.2$ V, $V_{CC} = 1.8$ V, SEL = H to L, SEL = L to H			300	
t _{BBM}	Break–Before–Make Time	R _L = 50 Ω, C _L = 5 pF, V _{SW} = 1.2 V, V _{CC} = 1.65 V to 4.5 V	10	50		ns
OIRR	Off Isolation for MIPI (Note 5)	$R_L = 50 \Omega$, f = 750 MHz, /OE = V _{CC} , V _{SW} = -1 dBm (200 mV _{PP}), V _{CC} = 1.65 V to 4.5 V		-30		dB
XTALK	Crosstalk for MIPI (Note 5)	$R_L = 50 \Omega$, f = 750 MHz, $V_{SW} = -1 \text{ dBm}$ (200 mV _{PP}), $V_{CC} = 1.65 V$ to 4.5 V		-38		dB
BW	Bandwidth at –3dB (Note 5)	R _L = 50 Ω, C _L = 0 pF, V _{CC} = 3 V		1.9		GHz
t _{SK(O)}	Channel-to-Channel Sin- gle-Ended Skew (Note 5)	TDR-Based Method (V _{SW} = 0.2 V _{PP} , C _L = C _{ON}), V _{CC} = 3.3 V		3	20	ps
t _{SK(P)}	Skew of Opposite Transi- tions of the Same Output (Note 5)	TDR-Based Method (V _{SW} = 0.2 V _{PP} , C _L = C _{ON}), V _{CC} = 3.3 V		3	20	ps

CAPACITANCE

C _{IN}	Control Pin Input Capaci- tance (Note 5)	V _{CC} = 0 V, f = 1 MHz	2.7	pF
C _{ON}	Out On Capacitance (Note 5)	V _{CC} = 3.3 V, /OE = 0 V, f = 1 MHz	4.3	pF
C _{OFF}	Out Off Capacitance (Note 5)	V_{CC} and /OE = 3.3 V, f = 1 MHz	1.9	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTE: Guarantee Levels:

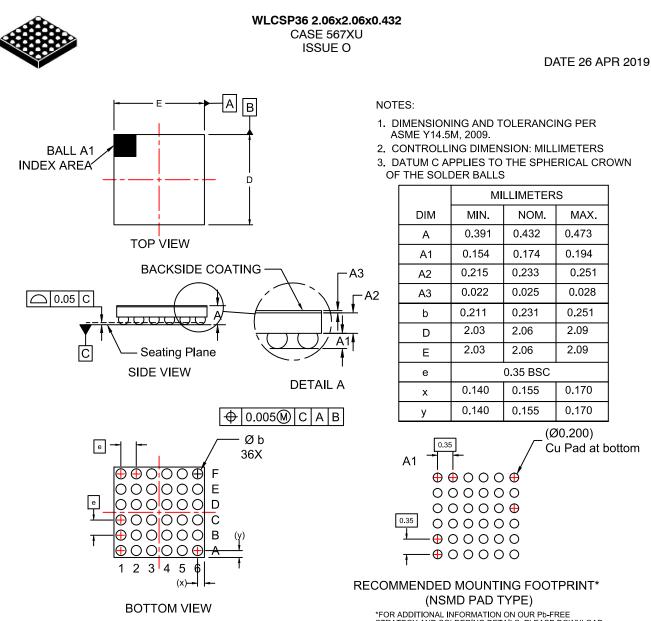
Guaranteed by Design. Characterized on the ATE or Bench.
Guaranteed by Design and Characterization, not Production Tested.

The table below pertains to the Packaging information on the following page.

ORDERING INFORMATION

Part Number	Operating Temperature Range	Package	Top Mark
FSA634UCX	-40 to +85°C	36–Ball WLCSP, Non–JEDEC 2.06 x 2.06 mm, 0.35 mm Pitch	VJ





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